

NCE N-Channel Super Trench Power MOSFET

Description

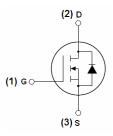
The NCEP02590T uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

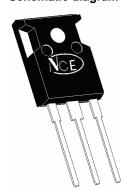
- $V_{DS} = 250V, I_{D} = 90A$ $R_{DS(ON)} < 15m\Omega @ V_{GS} = 10V$
- Excellent gate charge x R_{DS(on)} product
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- Optimized body diode reverse recovery performance

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



Schematic diagram



TO-247 top view

100% UIS TESTED! 100% ΔVds TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity	
NCEP02590T	NCEP02590T	TO-247-3L	-	-	-	

Absolute Maximum Ratings (T_C=25 ℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	250	V
Gate-Source Voltage	V _G S	±20	V
Drain Current-Continuous	I _D	90	А
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	63.6	Α
Pulsed Drain Current (Note 1)	I _{DM}	360	Α
Maximum Power Dissipation	P _D	330	W
Derating factor		2.2	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	1700	mJ
Operating Junction and Storage Temperature Range	T_{J},T_{STG}	-55 To 175	$^{\circ}$

Thermal Characteristic

Thermal Resistance,Junction-to-Case ^(Note 2)	R _{eJC}	0.45	°C/W
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Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	250		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =250V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.5		4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =45A	-	14	15	mΩ
Gate resistance	R_G		-	3.3	-	Ω
Forward Transconductance	g FS	V _{DS} =10V,I _D =45A	70	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	\/ -425\/\/ -0\/	-	6595	-	PF
Output Capacitance	C _{oss}	V_{DS} =125V, V_{GS} =0V, F=1.0MHz	-	409.5	-	PF
Reverse Transfer Capacitance	C _{rss}	F-1.UIVITZ	-	11	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	19.5	-	nS
Turn-on Rise Time	t _r	V_{DD} =125 V , I_D =45 A	-	28	-	nS
Turn-Off Delay Time	$t_{d(off)}$	V_{GS} =10 V , R_{G} =4.7 Ω	-	48	-	nS
Turn-Off Fall Time	t _f		-	15	-	nS
Total Gate Charge	Q_g	\/ -125\/ -45 \	-	90.9		nC
Gate-Source Charge	Q_{gs}	V _{DS} =125V,I _D =45A,	-	40.4		nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	18		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V _{GS} =0V,I _S =90A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	90	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 45A	-	204		nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	1.81		uC

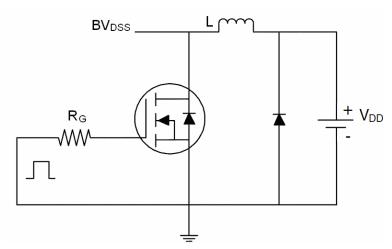
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\text{C}$,V $_{DD}$ =50 V ,V $_{G}$ =10 V ,L=0.5 mH ,Rg=25 Ω

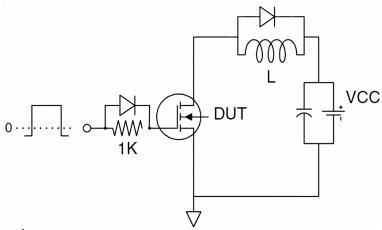


Test Circuit

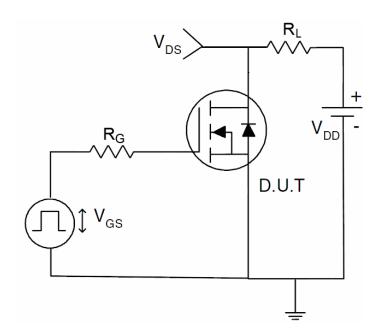
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics

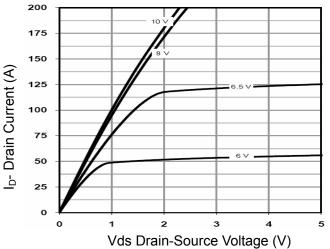


Figure 1 Output Characteristics

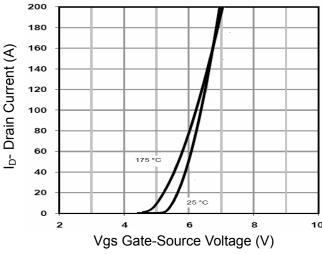


Figure 2 Transfer Characteristics

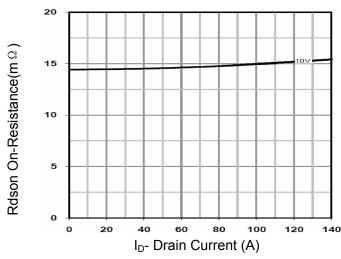


Figure 3 Rdson- Drain Current

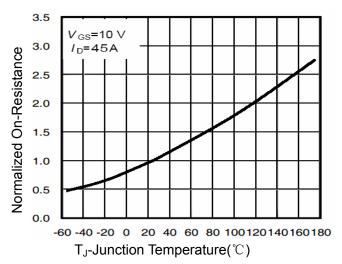


Figure 4 Rdson-JunctionTemperature

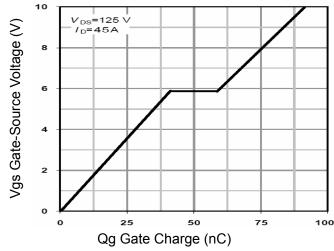


Figure 5 Gate Charge

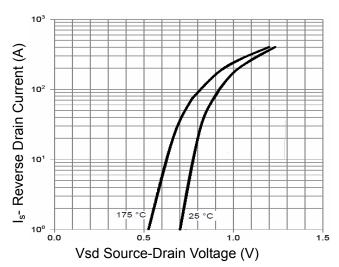


Figure 6 Source- Drain Diode Forward



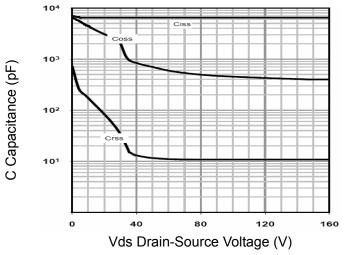


Figure 7 Capacitance vs Vds

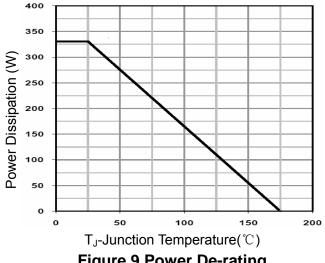


Figure 9 Power De-rating

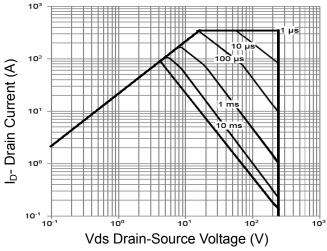


Figure 8 Safe Operation Area

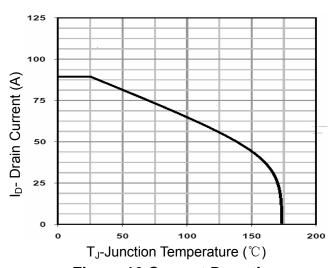


Figure 10 Current De-rating

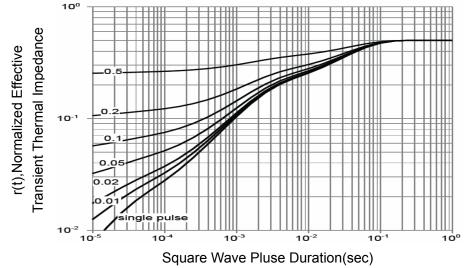
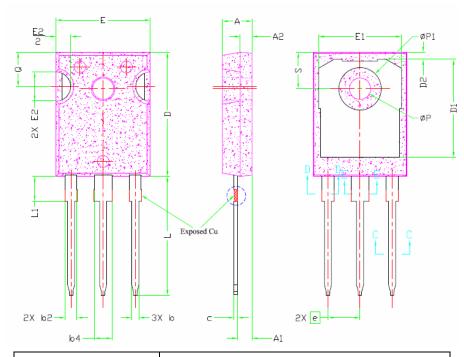


Figure 11 Normalized Maximum Transient Thermal Impedance



TO-247 Package Information



Symbol	Dimensions In Millimeters				
Symbol	Min.	Nom.	Max.		
А	4.83	5.02	5.21		
A1	2.29	2.41	2.55		
A2	1.50	2.00	2.49		
b	1.12	1.20	1.33		
b1	1.12	1.20	1.28		
b2	1.91	2.00	2.39		
b3	1.91	2.00	2.34		
b4	2.87	3.00	3.22		
b5	2.87	3.00	3.18		
С	0.55	0.60	0.69		
c1	0.55	0.60	0.65		
D	20.80	20.95	21.1		
D1	16.25	16.55	17.65		
D2	0.51	1.19	1.35		
Е	15.75	15.94	16.13		
E1	13.46	14.02	14.16		
E2	4.32	4.91	5.49		
L	19.81	20.07	20.32		
L1	4.10	4.19	4.40		
Q	5.39	5.79	6.20		
ФР	3.56	3.61	3.65		
S	6.04	6.17	6.30		

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NCEP02590T

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